



P-Channel 1.5-V (G-S) MOSFET

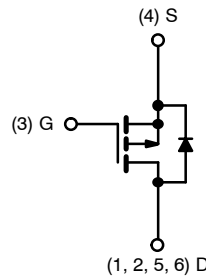
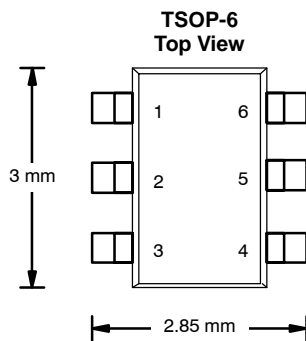
PRODUCT SUMMARY			
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)	Q _g (Typ)
-8	0.023 @ V _{GS} = -4.5 V	-7	28
	0.029 @ V _{GS} = -2.5 V	-6.2	
	0.036 @ V _{GS} = -1.8 V	-5.2	
	0.048 @ V _{GS} = -1.5 V	-5.0	

FEATURES

- TrenchFET® Power MOSFET: 1.5-V Rated
- Ultra-Low On-Resistance
- 100% R_g Tested

APPLICATIONS

- Load Switch for Portable Devices



P-Channel MOSFET

Ordering Information: Si3499DV-T1—E3
Marking Code: B3xxx

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	5 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	-8		V
Gate-Source Voltage		V _{GS}	±5		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	-7	-5.3	A
	T _A = 85 °C		-3.6	-3.9	
Pulsed Drain Current		I _{DM}	-20		
Continuous Diode Current (Diode Conduction) ^a		I _S	-1.7	-0.9	
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	2.0	1.1	W
	T _A = 85 °C		1.0	0.6	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 5 sec	R _{thJA}	45	62.5	°C/W
	Steady State		90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	25	30	

Notes
a. Surface Mounted on 1" x 1" FR4 Board.

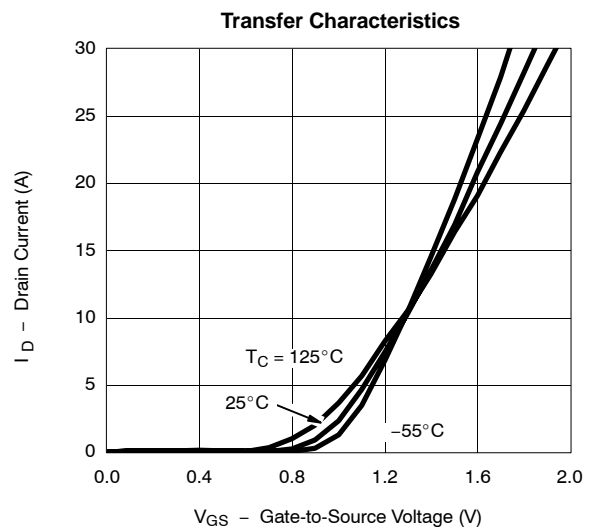
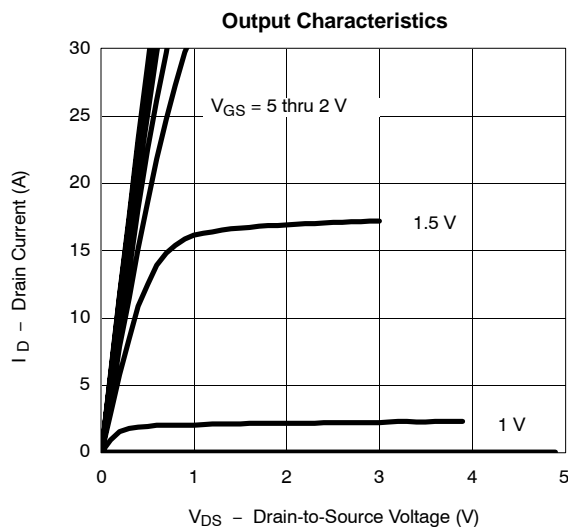

SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.35		-0.75	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±5 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -8 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -8 V, V _{GS} = 0 V, T _J = 85 °C			-10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = -5 V, V _{GS} = -4.5 V	-20			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = -4.5 V, I _D = -7 A		0.019	0.023	Ω
		V _{GS} = -2.5 V, I _D = -6.2 A		0.024	0.029	
		V _{GS} = -1.8 V, I _D = -5.2 A		0.028	0.036	
		V _{GS} = -1.5 V, I _D = -3 A		0.035	0.048	
Forward Transconductance ^a	g _{fs}	V _{DS} = -5 V, I _D = -7 A		28		S
Diode Forward Voltage ^a	V _{SD}	I _S = -1.7 A, V _{GS} = 0 V		-0.63	-1.1	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = -4 V, V _{GS} = -4.5 V, I _D = -7 A		28	42	nC
Gate-Source Charge	Q _{gs}			2.9		
Gate-Drain Charge	Q _{gd}			5.8		
Gate Resistance	R _g		4	8.5	13	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = -4 V, R _L = 4 Ω I _D ≅ -1 A, V _{GEN} = -4.5 V, R _g = 6 Ω		27	40	ns
Rise Time	t _r			65	100	
Turn-Off Delay Time	t _{d(off)}			210	315	
Fall Time	t _f			110	165	
Source-Drain Reverse Recovery Time	t _{rr}		I _F = -1.7 A, di/dt = 100 A/μs		40	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
 b. Guaranteed by design, not subject to production testing.

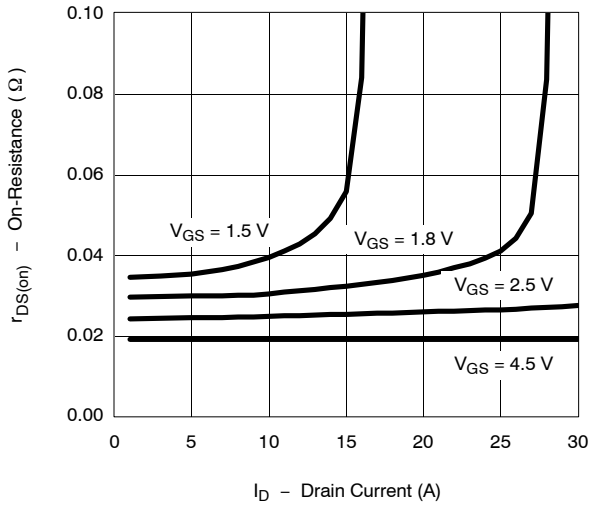
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)


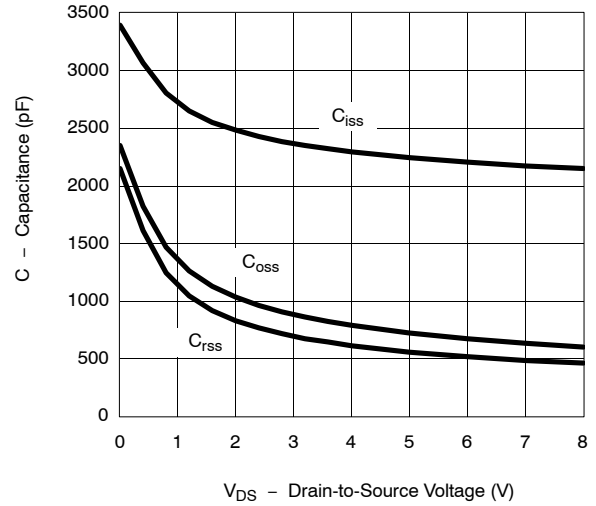


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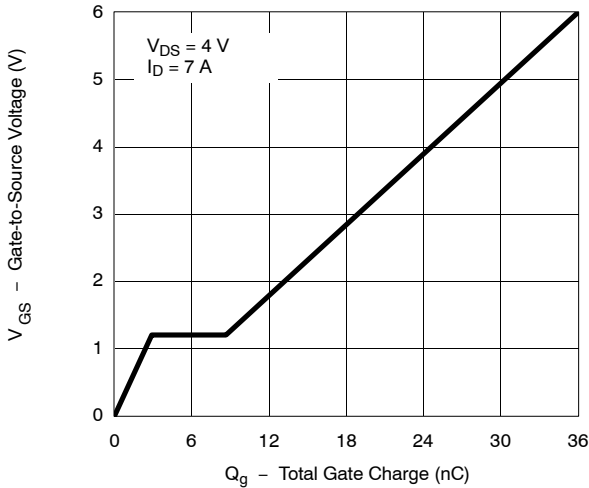
On-Resistance vs. Drain Current



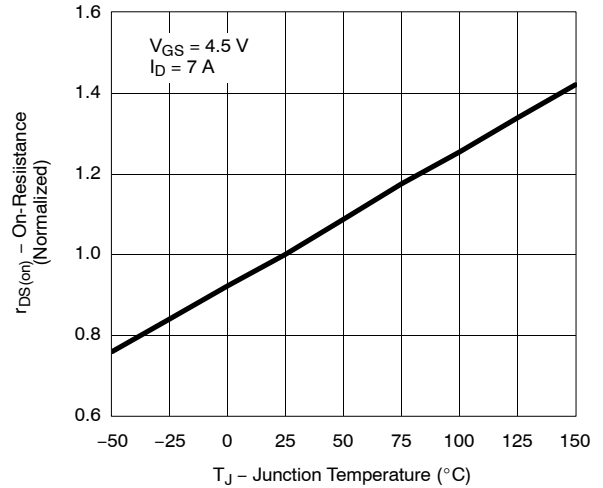
Capacitance



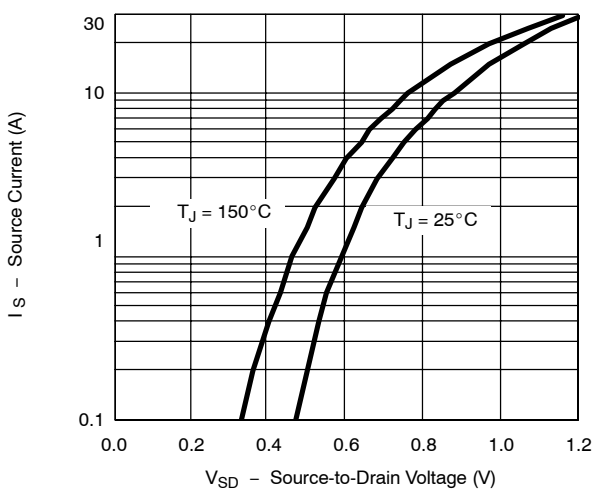
Gate Charge



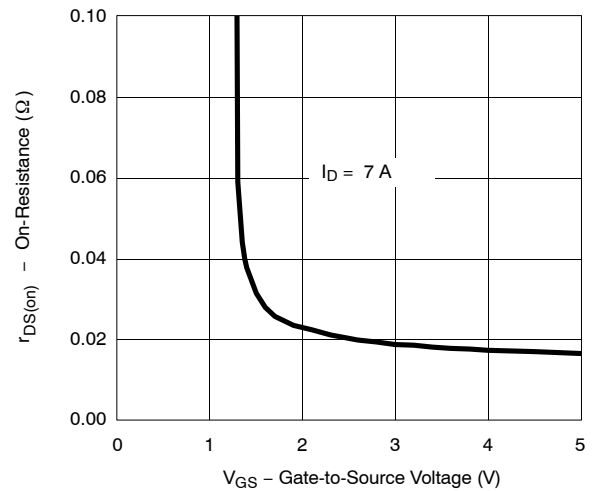
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

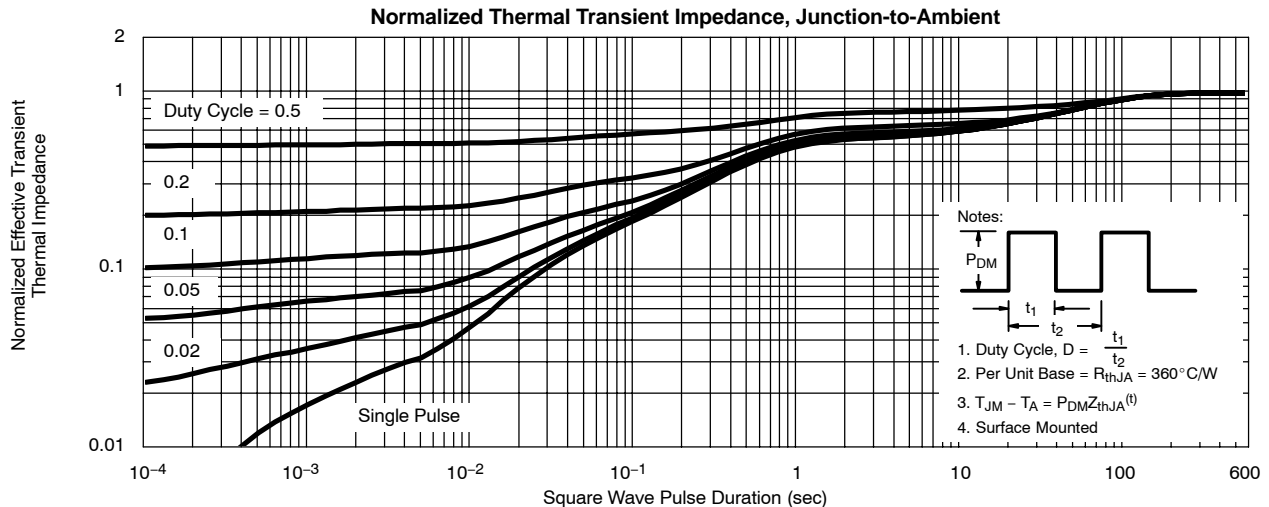
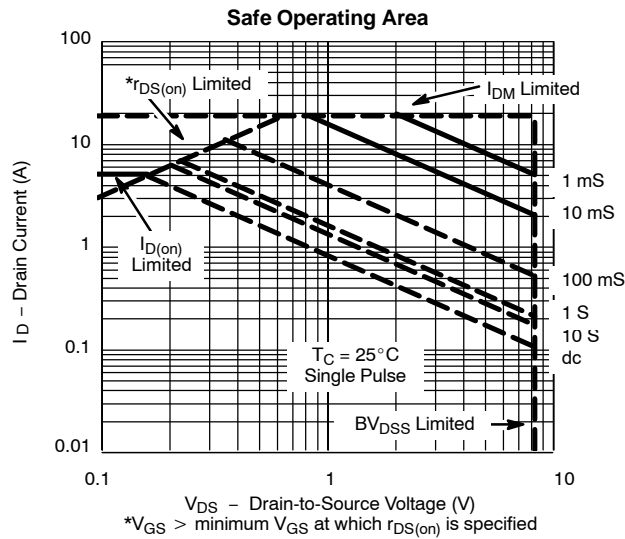
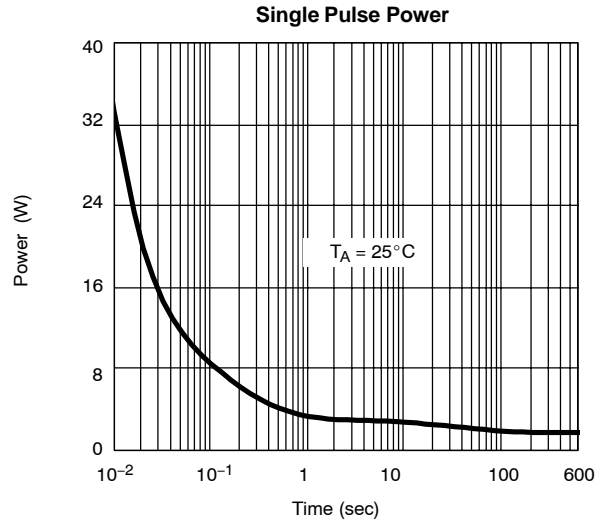
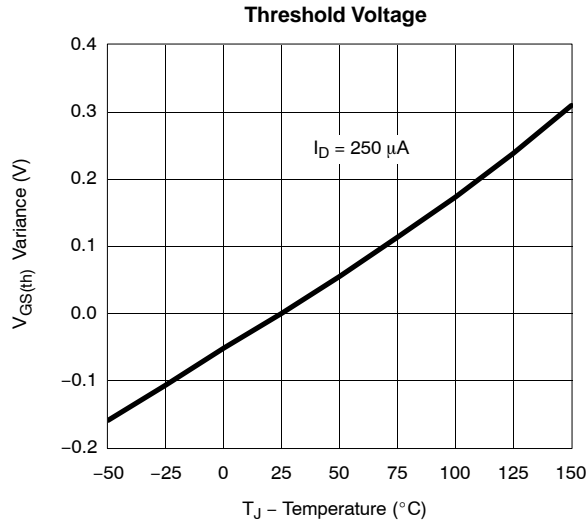


On-Resistance vs. Gate-to-Source Voltage



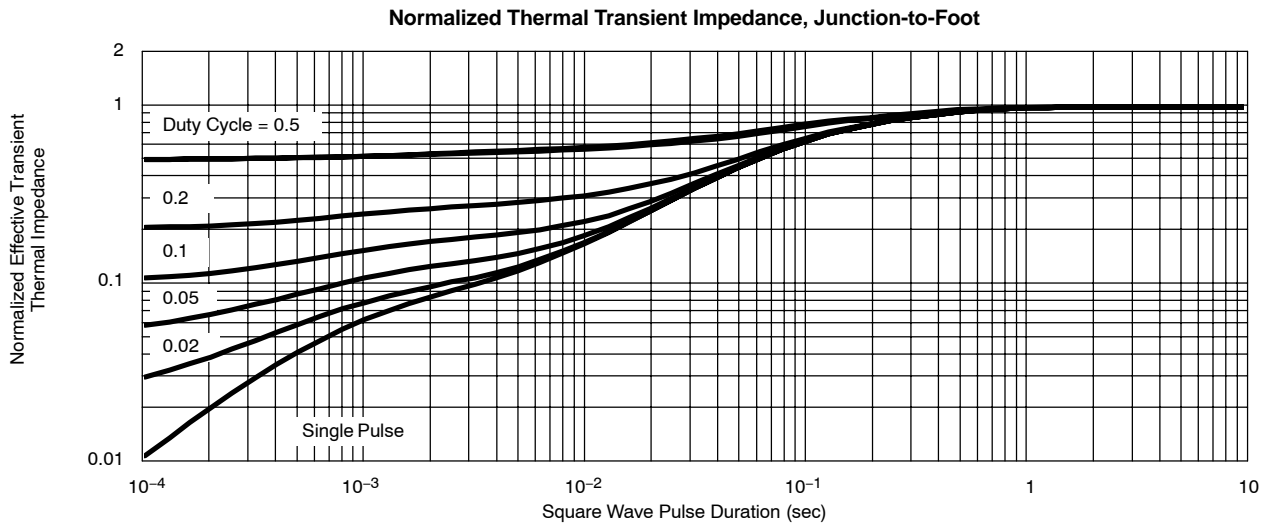


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